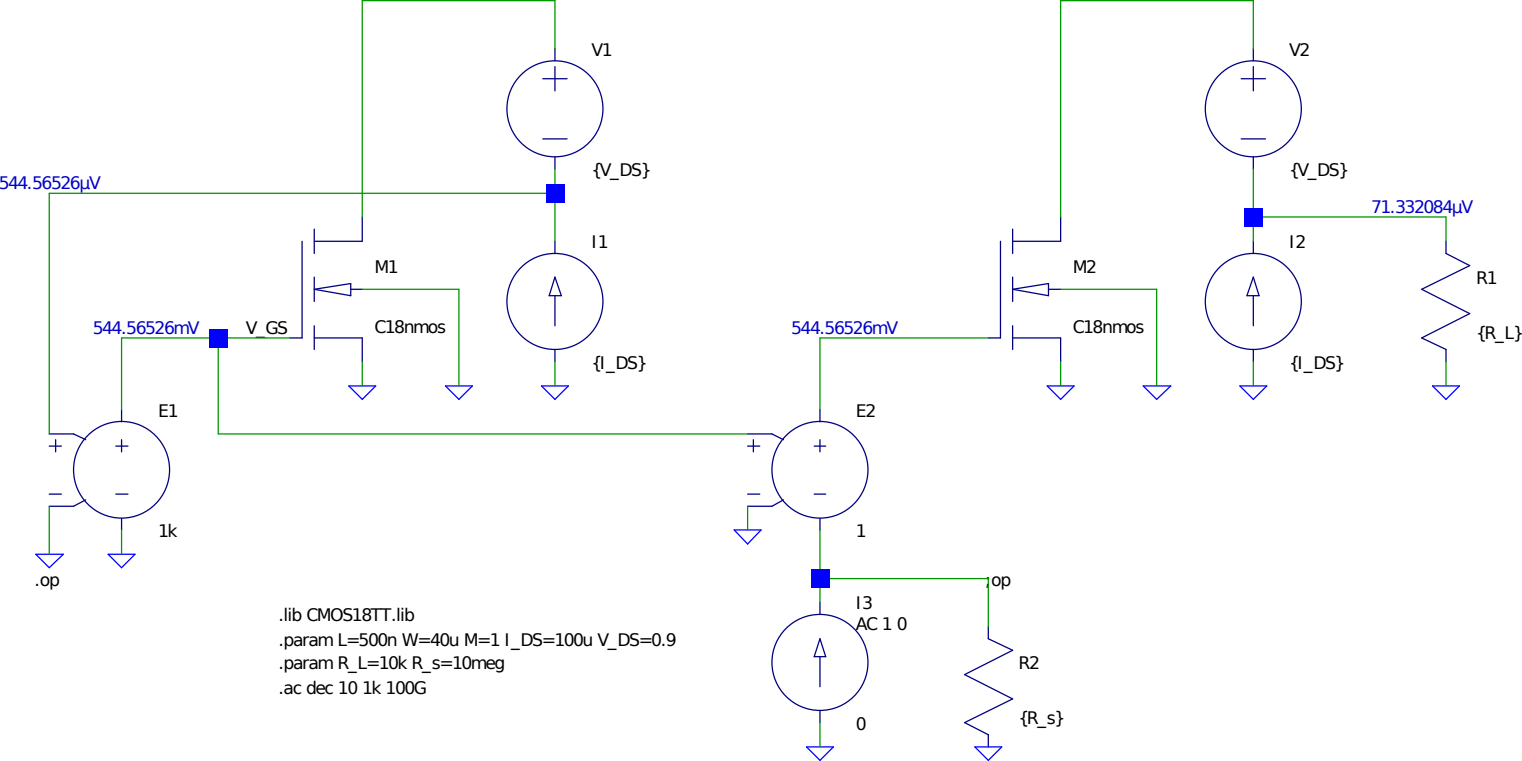
V1
{V_DS}
544.56526µV
I1
M1
544.56526mV
V_GS
C18nmos
{I_DS}
E1
1k
.op
V2
{V_DS}
71.332084µV
I2
R1
M2
544.56526mV
C18nmos
{I_DS}
{R_L}
E2
1
.op
I3
AC 1 0
R2
0
{R_s}
.lib CMOS18TT.lib
.param L=500n W=40u M=1 I_DS=100u V_DS=0.9
.param R_L=10k R_s=10meg
.ac dec 10 1k 100G